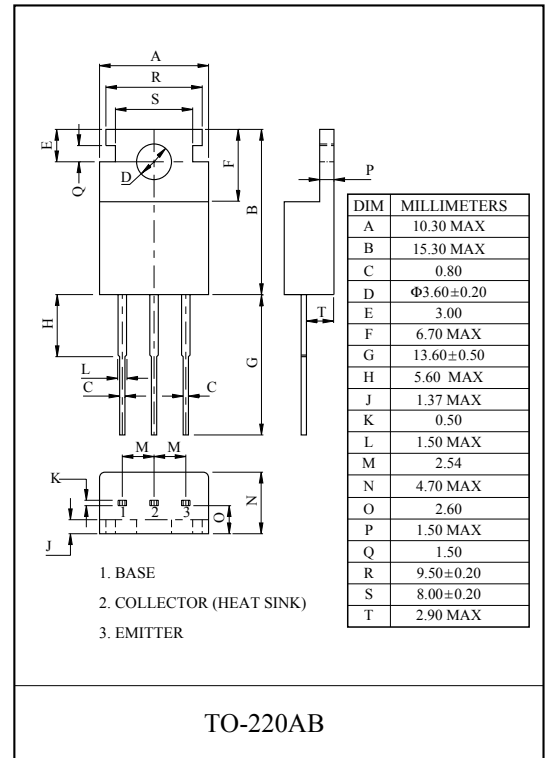


HIGH VOLTAGE AND HIGH RELIABILITY
HIGH SPEED SWITCHING, WIDE SOA

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	1100	V
Collector-Emitter Voltage		V_{CEO}	800	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	1.5	A
	Pulse	I_C	5	
Base Current		I_B	0.8	A
Collector Power Dissipation (Tc=25°C)		P_C	40	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55 ~ 150	°C



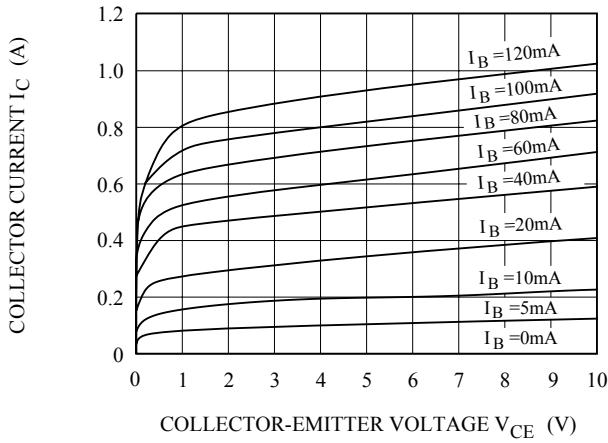
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=800V, I_E=0$	-	-	10	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	10	μA
Collector-Emitter Sustaining Voltage		$V_{CEX(SUS)}$	$I_C=0.75A, I_{B1}=-I_{B2}=0.15A$ $L=5mH, Clamped$	800	-	-	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=0.75A, I_B=0.15A$	-	-	2	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C=0.75A, I_B=0.15A$	-	-	1.5	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=5V, I_C=0.1A$	15	-	40		
	$h_{FE(2)}$	$V_{CE}=5V, I_C=0.5A$	8	-	-		
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	1100	-	-	V
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	800	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7	-	-	V
Collector Output Capacitance		C_{ob}	$V_{CB}=10V, f=1MHz, I_E=0$	-	35	-	pF
Transition Frequency		f_T	$V_{CE}=10V, I_C=0.1A$	-	15	-	MHz
Switching Time	Turn On Time	t_{on}	<p>$I_{B1}=0.2A, I_{B2}=-0.4A$ DUTY CYCLE ≤ 1%</p>	-	-	0.5	μS
	Storage Time	t_{stg}		-	-	3	
	Fall Time	t_f		-	-	0.3	

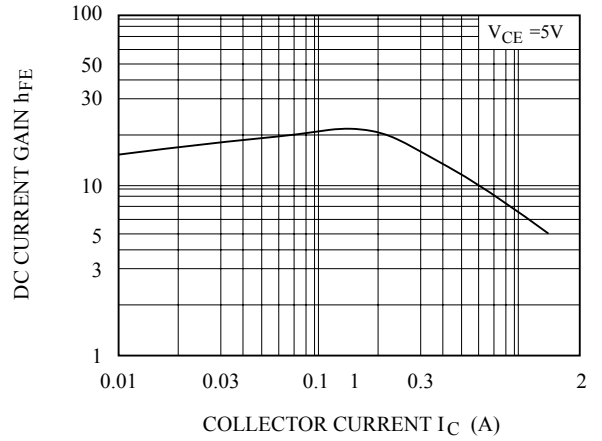
Note : $h_{FE(1)}$ Classification R:15 ~ 30, O:20 ~ 40

KTC4526

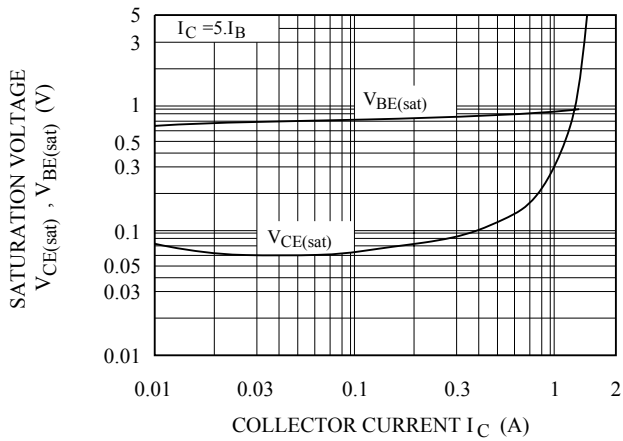
$I_C - V_{CE}$



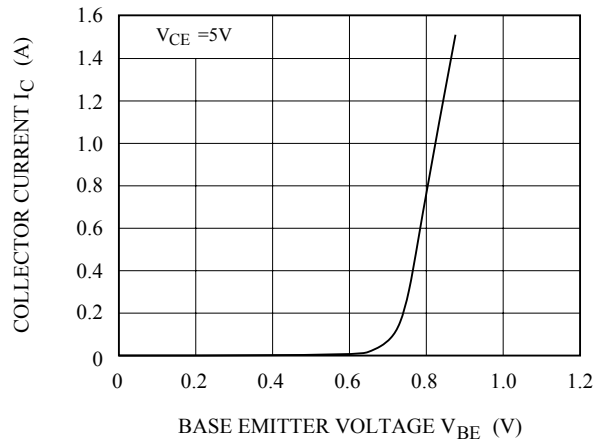
$h_{FE} - I_C$



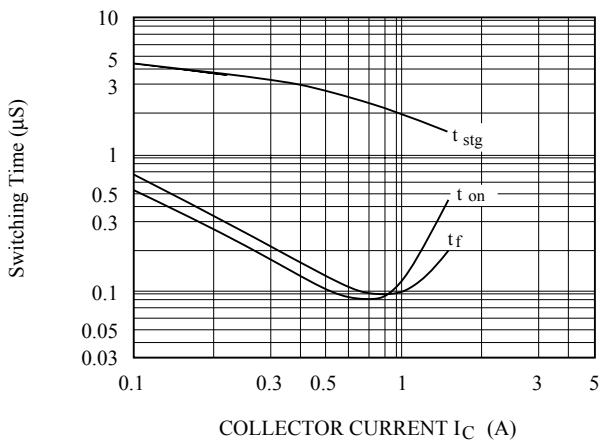
$V_{CE(sat)}, V_{BE(sat)} - I_C$



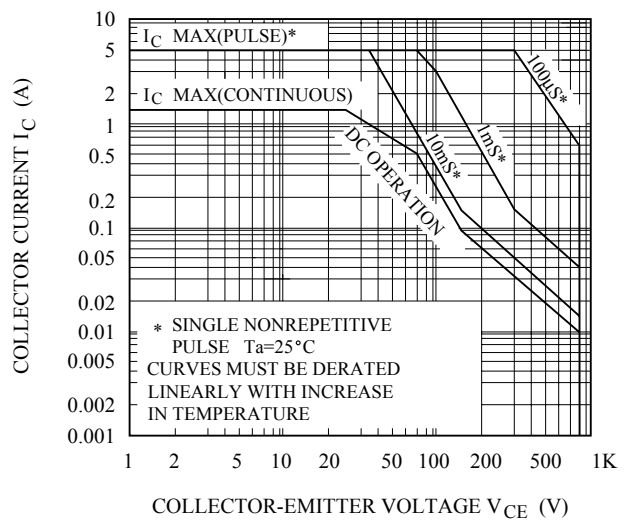
$I_C - V_{BE}$



SWITCHING CHARACTERISTICS

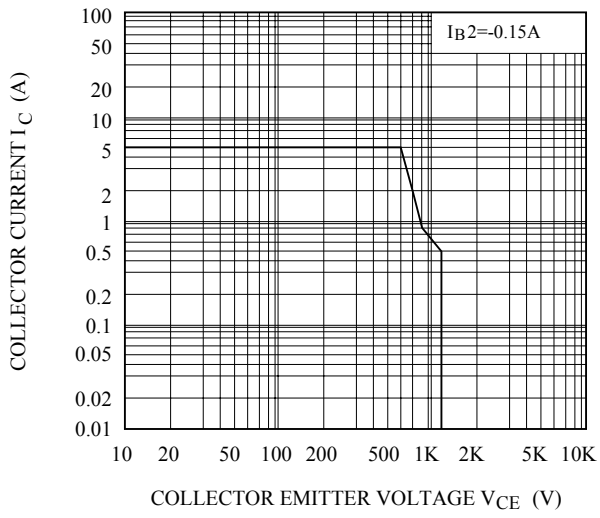


SAFE OPERATING AREA



KTC4526

REVERSE BIAS SAFE OPERATING AREA



$P_c - T_a$

